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Application No.: 10/811,808

Docket No.: 2336-257

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A GaN-based semiconductor light emitting diode, comprising:

a substrate on which a GaN-based semiconductor material is grown;

a lower clad layer formed on the substrate, and made of a first conductive GaN semiconductor material;

an active layer formed on a designated portion of the lower clad layer, and made of ZnNi an ~~undoped GaN semiconductor material~~;

an upper clad layer formed on the active layer, and made of a second conductive GaN semiconductor material;

an alloy layer formed on the upper clad layer, and made of an alloy selected from the group consisting of La-based alloy and Ni-based alloy; and

an TCO(Transparent Conduct Oxide) layer formed on the alloy layer.

2. (original) The GaN-based semiconductor light emitting diode as set forth in claim 1, wherein the alloy layer has a thickness of 100Å or less.

3-4. (canceled)

5. (original) The GaN-based semiconductor light emitting diode as set forth in claim 1, wherein the TCO(Transparent Conduct Oxide) layer is made of at least one material

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selected from the group consisting of ITO, ZnO, Indium Oxide and MgO.

6-14. (canceled)